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Inclosure Material:	
Plastic	
Overall Length:	
Between 0.170 inches	s and 0.210 inches
Terminal Length:	
0.500 inches	
Overall Height:	
Between 0.125 inches	s and 0.165 inches
Overall Width:	
Between 0.175 inches	s and 0.205 inches
Function For Which	Designed:
Phototransistor	
Internal Configuration	on:
Junction contact-darli	ngton connected
Joint Electronic Dev	ice Engineering Council/jedec/case Outline Designation:
То-98	
Response Time:	
250.0 microseconds	
Mounting Method:	
Terminal	
Semiconductor Mate	erial:
Silicon	
Voltage Rating In Vo	Its Per Characteristic:
8.0 emitter to base ve	oltage, static, collector open and 25.0 collector to base voltage/static/emitter open and 25.0 collector to emitter
voltage/static/base op	en
Current Rating Per (Characteristic:
250.00 milliamperes p	beak forward surge current
Power Rating Per Cl	naracteristic:
200.0 milliwatts small	-signal input power, common-collector preset
Maximum Operating	Tempurature Per Measurement Point:
100.0 degrees celsius	junction
Special Features:	
Junction pattern arrar	igement: npn
Terminal Type And	Quantity:
3 uninsulated wire lea	d
Specification Data:	
80131-release6060 p	rofessional/industrial association specification
Shelf Life:	
N/a	
Unit Of Measure:	
 Demilitarization:	
No	

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